#### 2N3903 2N3904

### **NPN SILICON TRANSISTOR**

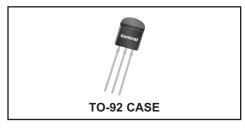


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## **DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N3903 and 2N3904 types are NPN silicon transistors designed for general purpose amplifier and switching applications. PNP complementary types are 2N3905 and 2N3906.





MAXIMUM RATINGS: (T <sub>A</sub> =25°C)	SYMBOL		UNITS
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Continuous Collector Current	$I_{C}$	200	mA
Power Dissipation	$P_{D}$	625	mW
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	$\Theta_{\sf JA}$	200	°C/W

ELECTRICAL	CHARACTERISTICS: (T <sub>A</sub> =25°C)	2N3	903	2N3	904	
SYMBOL	TEST CONDITIONS \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	MIN	MAX	MIN	MAX	UNITS
ICEV	$V_{CE}$ =30V, $V_{EB}$ =3.0V	-	50	-	50	nA
BV <sub>CBO</sub>	I <sub>C</sub> =10μA	60	-	60	-	V
BV <sub>CEO</sub>	I <sub>C</sub> =1.0mA	40	-	40	-	V
BVEBO	I <sub>E</sub> =10μA	6.0	-	6.0	-	V
V <sub>CE</sub> (SAT)	I <sub>C</sub> =10mA, I <sub>B</sub> =1.0mA	-	0.2	-	0.2	V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5.0mA	-	0.3	-	0.3	V
V <sub>BE</sub> (SAT)	I <sub>C</sub> =10mA, I <sub>B</sub> =1.0mA	0.65	0.85	0.65	0.85	V
V <sub>BE</sub> (SAT)	I <sub>C</sub> =50mA, I <sub>B</sub> =5.0mA	-	0.95	-	0.95	V
h <sub>FE</sub> ` ´	$V_{CE}$ =1.0V, $I_{C}$ =0.1mA	20	-	40	-	
hFE	V <sub>CE</sub> =1.0V, I <sub>C</sub> =1.0mA	35	-	70	-	
hFE	V <sub>CE</sub> =1.0V, I <sub>C</sub> =10mA	50	150	100	300	
h <sub>FE</sub>	$V_{CE}$ =1.0V, $I_{C}$ =50mA	30	-	60	-	
hFE	$V_{CE}$ =1.0V, $I_{C}$ =100mA	15	-	30	-	
h <sub>fe</sub>	$V_{CE}$ =10V, $I_{C}$ =1.0mA, f=1.0kHz	50	200	100	400	
f <sub>T</sub>	$V_{CE}$ =20V, $I_{C}$ =10mA, f=100MHz	250	-	300	-	MHz
C <sub>ob</sub>	$V_{CB}$ =5.0V, $I_{E}$ =0, f=100kHz	-	4.0	-	4.0	pF
C <sub>ib</sub>	$V_{EB}$ =0.5V, $I_{C}$ =0, f=100kHz	-	8.0	-	8.0	pF
NF	$V_{CE}$ =5.0V, $I_{C}$ =100 $\mu$ A, $R_{S}$ =1.0 $k\Omega$					
	f=10Hz to 15.7kHz	-	6.0	-	5.0	dB
t <sub>on</sub>	$V_{CC}$ =3.0V, $V_{BE(OFF)}$ =0.5V, $I_{C}$ =10mA					
	I <sub>B1</sub> =1.0mA	-	70	-	70	ns
t <sub>off</sub>	V <sub>CC</sub> =3.0V, I <sub>C</sub> =10mA, I <sub>B1</sub> =I <sub>B2</sub> =1.0mA	-	225	-	250	ns

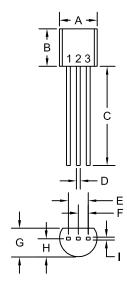
R2 (12-October 2011)

# 2N3903 2N3904

### **NPN SILICON TRANSISTOR**



### **TO-92 CASE - MECHANICAL OUTLINE**



DIMENSIONS							
	INCHES		MILLIMETERS				
SYMBOL	MIN	MAX	MIN	MAX			
A (DIA)	0.175	0.205	4.45	5.21			
В	0.170	0.210	4.32	5.33			
С	0.500	_	12.70	-			
D	0.016	0.022	0.41	0.56			
Е	0.100		2.54				
F	0.050		1.27				
G	0.125	0.165	3.18	4.19			
Н	0.080	0.105	2.03	2.67			
	0.015		0.38				

TO-92 (REV: R1)

### LEAD CODE:

- 1) Emitter 2) Base 3) Collector

## MARKING:

R1

**FULL PART NUMBER**